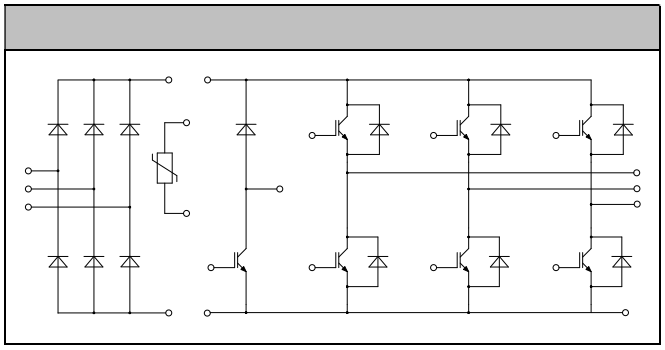
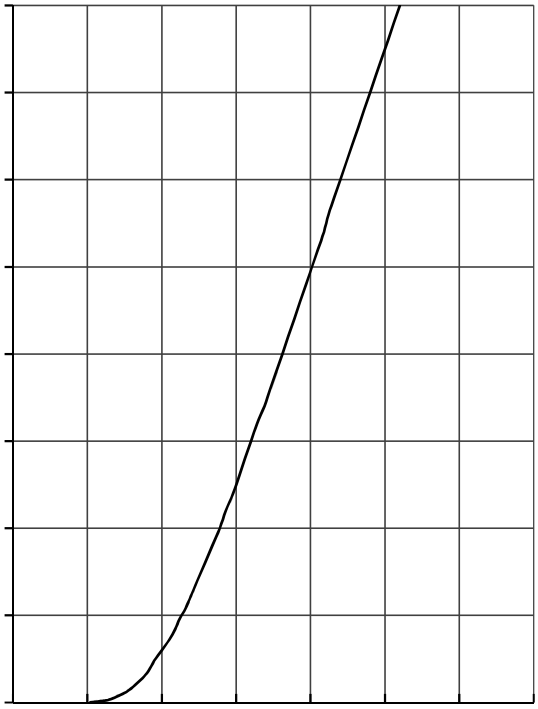
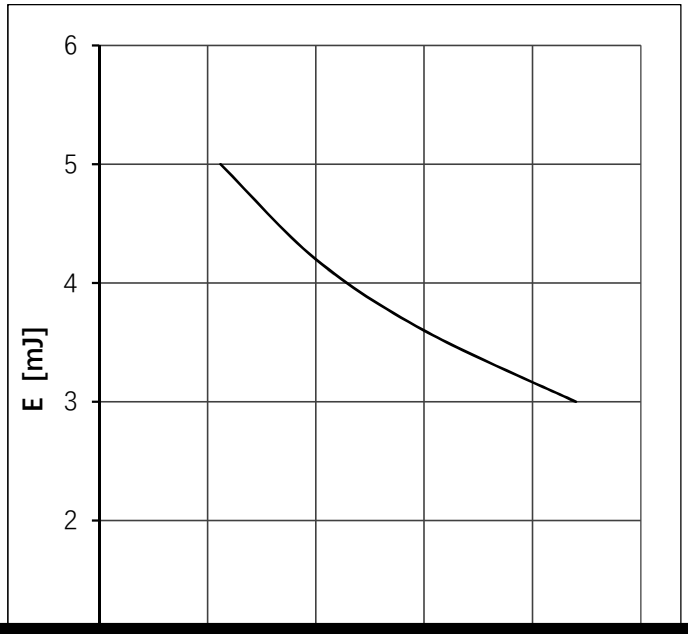


℃

		℃				
		℃				

Isolation voltage	V	t=1min,f=50Hz	2500			V
Maximum Junction Temperature	T				175	
Operating Junction Temperature	T		-40		150	
Storage Temperature	T		-40		125	
Stray-inductance-module	L			60		
Module lead resistance, terminals-chip	R	T =25 , per switch		4.0		
	R			3.0		
Thermal Resistance Junction-to Case	R	per IGBT-inverter			0.27	K/W
		per Diode-inverter			0.50	
		per IGBT-brake-copper			0.34	
		per Diode-chopper			1.20	
		per Diode-rectifier			0.43	
Thermal Resistance Case-to Sink	R	per IGBT-inverter		0.12		K/W
		per Diode-inverter		0.22		
		per IGBT-brake-copper		0.14		
		per Diode-chopper		0.56		
		per Diode-rectifier		0.19		
		per Module		0.009		
Mounting Force Per Clamp	F		3.0		6.0	N
Weight of Module	G			300		g





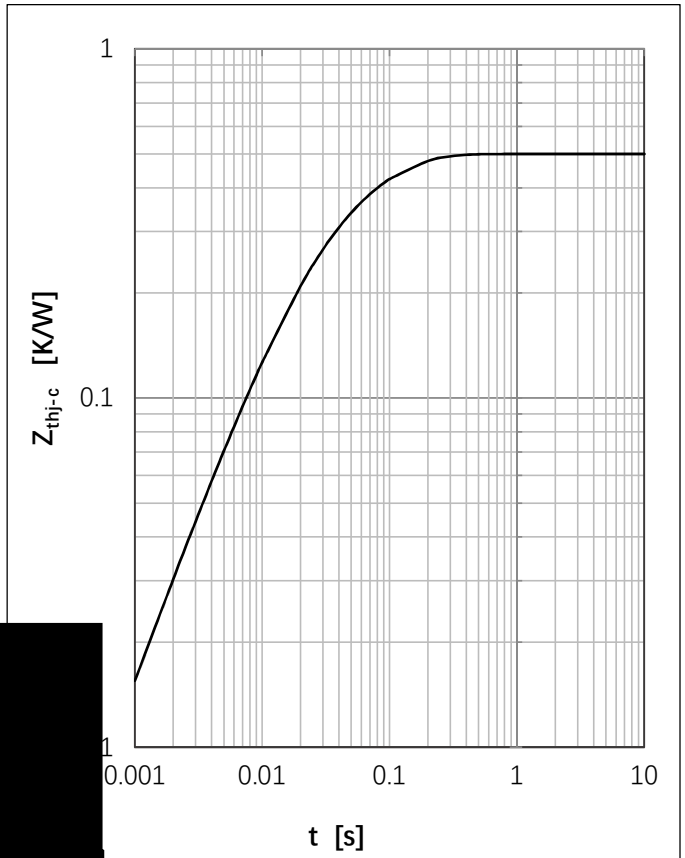


Fig10.Diode Transient Thermal Impedance

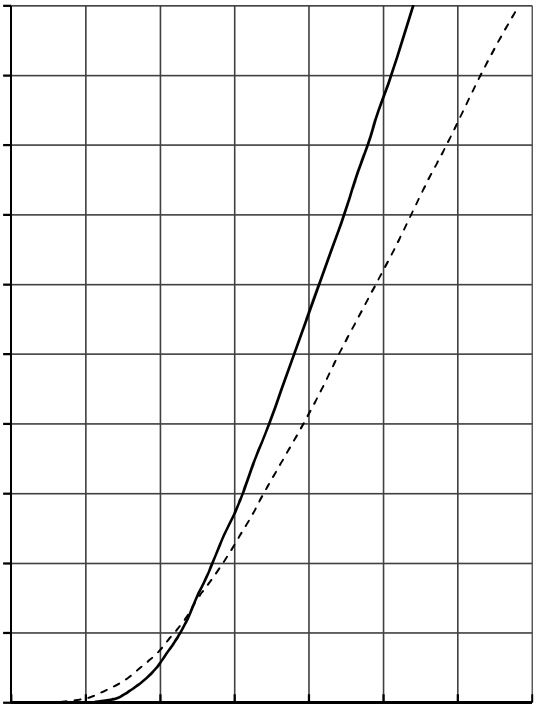


Fig 11. NTC Temperature Characteristic

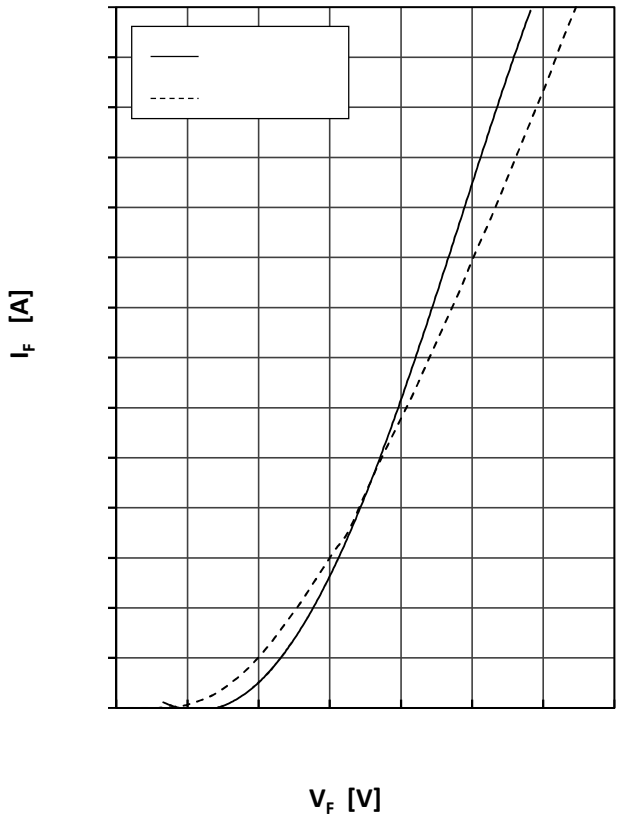


Fig13. Diode-brake-chopper Forward Characteristics